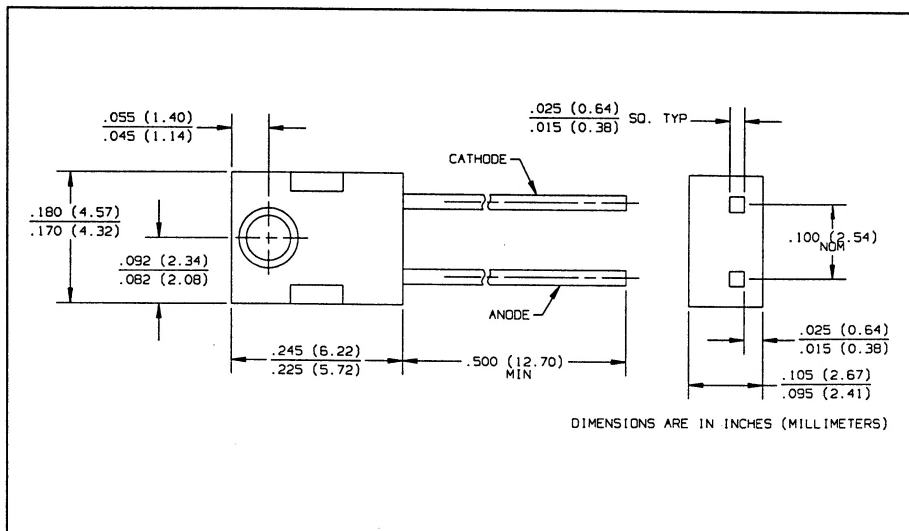
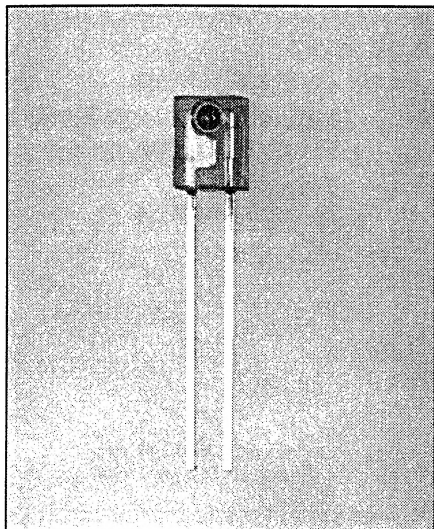


GaAlAs Plastic Infrared Emitting Diodes Types OP245A, OP245B, OP245C, OP245D



Features

- Mechanically and spectrally matched to the OP555 and OP565 series devices
- Wavelength matched to silicon's peak response
- Significantly higher power output than GaAs at equivalent drive currents
- Side-looking package for space limited applications

Description

The OP245 series devices are 890 nm high intensity gallium aluminum arsenide infrared emitting diodes molded in IR transmissive amber tinted epoxy packages. The side-looking packages are for use in PC board mounted slotted switches or as easily mounted interrupt detectors.

Replaces

K6650

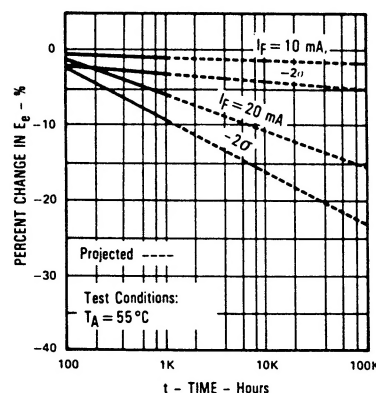
Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Reverse Voltage	2.0 V
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Storage and Operating Temperature Range	-40°C to $+100^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	100 mW ⁽²⁾

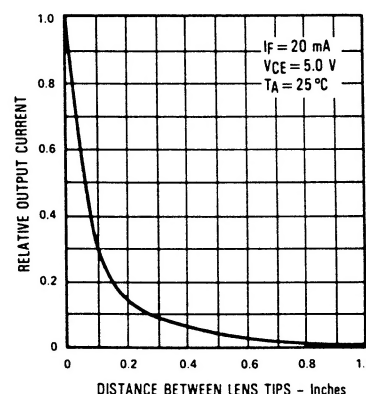
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering. A max. of 20 grams force may be applied to the leads when soldering.
- (2) Derate linearly 1.33 mW/ $^\circ\text{C}$ above 25°C .
- (3) $E_{e(\text{APT})}$ is a measurement of the average apertured radiant incidence upon a sensing area 0.180" (4.57 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 0.653" (16.6 mm) from the lens tip. $E_{e(\text{APT})}$ is not necessarily uniform within the measured area.

Typical Performance Curves Percent Changes in Radiant Intensity vs Time



Coupling Characteristics of OP245 and OP555



Types OP245A, OP245B, OP245C, OP245D

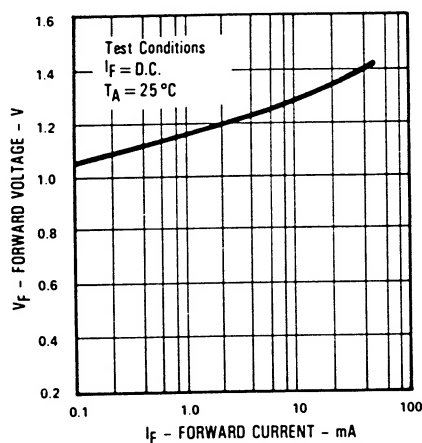
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$E_e(\text{APT})$	Apertured Radiant Incidence	OP245D 0.05 OP245C 0.20 OP245B 0.40 OP245A 0.60		0.86 1.20	mW/cm^2 mW/cm^2 mW/cm^2 mW/cm^2	$I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$ $I_F = 20\text{ mA}^{(3)}$
V_F	Forward Voltage			1.80	V	$I_F = 20\text{ mA}$
I_R	Reverse Current			100	μA	$V_R = 2\text{ V}$
λ_p	Wavelength at Peak Emission		890		nm	$I_F = 10\text{ mA}$
B	Spectral Bandwidth Between Half Power Points		80		nm	$I_F = 10\text{ mA}$
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature		+0.18		$\text{nm}/^\circ\text{C}$	$I_F = \text{Constant}$
θ_{HP}	Emission Angle at Half Power Points		40		Deg.	$I_F = 20\text{ mA}$
t_r	Output Rise Time		500		ns	$I_F(\text{PK}) = 100\text{ mA}$, $\text{PW} = 10\text{ }\mu\text{s}$, D.C. = 10%
t_f	Output Fall Time		250		ns	

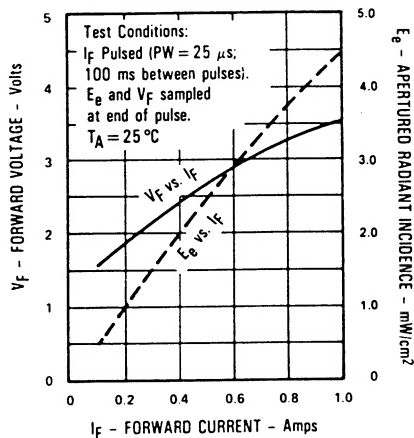
INFRARED
EMITTING
DIODES

Typical Performance Curves

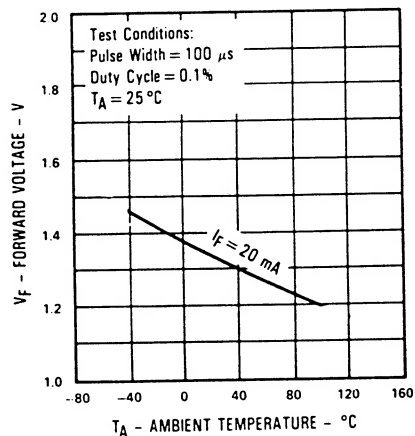
Forward Voltage vs
Forward Current



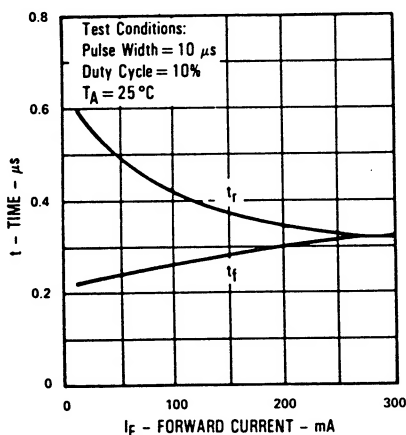
Forward Voltage and Radiant Incidence
vs Forward Current



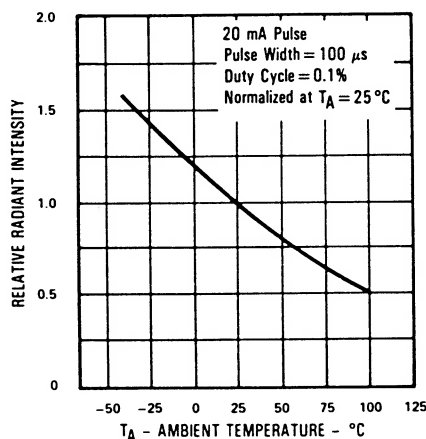
Forward Voltage vs
Ambient Temperature



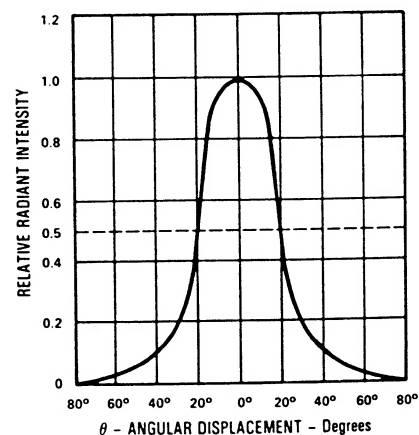
Rise Time and Fall Time vs
Forward Current



Relative Radiant Intensity
vs Ambient Temperature



Relative Radiant Intensity vs
Angular Displacement



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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